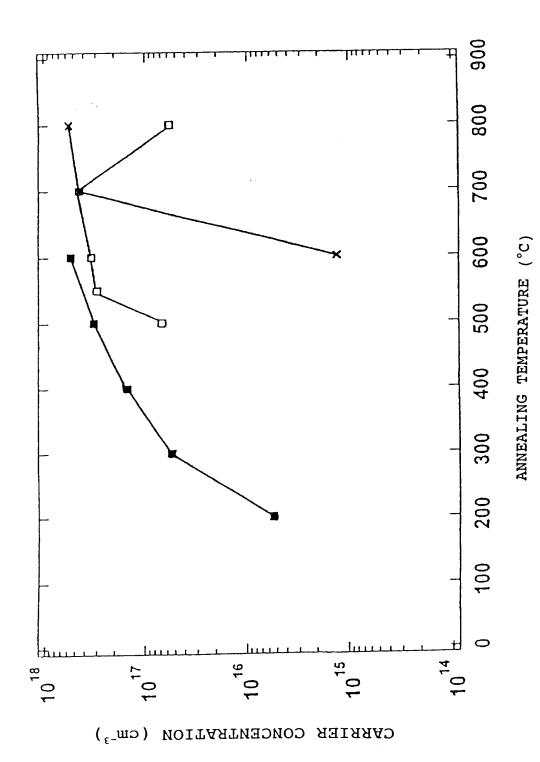


ВY

\ 57

Fíg. 2



MIKI et al Q61744
METHOD FOR PRODUCING P-TYPE GALLIUM NITRIDE-BASED
OMPOUND SEMICONDUCTOR, METHOD FOR PRODUCING
LLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR
GITT-EMITTING DEVICE.
Bruce E. Kramer
Fided July 10, 2001 202-293-7060
3 of 4

Fig. 3

MIKE et al. Q61744
METHOD FOR PRODUCING P-TYPE GALLIUM NITRIDE BASED
OMFOUND SEMICONDICTOR, METHOD FOR PRODUCING
ILLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR
OHT-EMITTING DEVICE.
Fried July (0, 200) 202-293-7000
4-614

